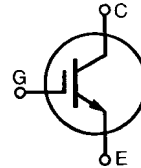


High Voltage IGBT

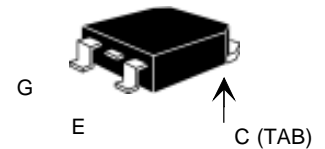
IXGH 24N170
IXGT 24N170

$V_{CES} = 1700 \text{ V}$
 $I_{C25} = 50 \text{ A}$
 $V_{CE(sat)} = 3.3 \text{ V}$
 $t_{fi(typ)} = 290 \text{ ns}$

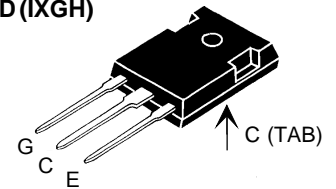


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	1700	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1 \text{ M}\Omega$	1700	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	50	A
I_{C90}	$T_C = 90^\circ\text{C}$	24	A
I_{CM}	$T_C = 25^\circ\text{C}, 1 \text{ ms}$	150	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 5 \Omega$ Clamped inductive load	$I_{CM} = 50$ @ $0.8 V_{CES}$	A
P_C	$T_C = 25^\circ\text{C}$	250	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
Maximum Lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
Maximum Tab temperature for soldering SMD devices for 10 s		260	$^\circ\text{C}$
M_d	Mounting torque (M3)	1.13/10Nm/lb.in.	
Weight		TO-247 AD	6 g
		TO-268	4 g

TO-268 (IXGT)



TO-247 AD (IXGH)



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features

- International standard packages JEDEC TO-268 and JEDEC TO-247 AD
- High current handling capability
- MOS Gate turn-on - drive simplicity
- Rugged NPT structure
- Molding epoxies meet UL 94 V-0 flammability classification

Applications

- Capacitor discharge & pulser circuits
- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies

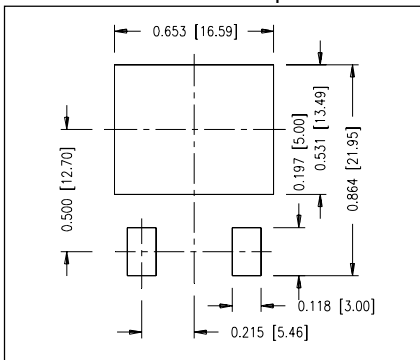
Advantages

- High power density
- Suitable for surface mounting
- Easy to mount with 1 screw, (isolated mounting screw hole)

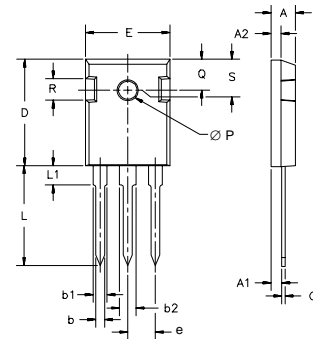
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 250 \mu\text{A}, V_{GE} = 0 \text{ V}$	1700		V
$V_{GE(th)}$	$I_C = 250 \mu\text{A}, V_{CE} = V_{GE}$	3.0		V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0 \text{ V}$			50 μA 500 μA
I_{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}, V_{GE} = 15 \text{ V}$			2.5 V 3.0 V

Symbol	Test Conditions	Characteristic Values			
		$(T_J = 25^\circ\text{C}, \text{ unless otherwise specified})$			
		min.	typ.	max.	
g_{fs}	$I_C = I_{C90}, V_{CE} = 10\text{ V}$ Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$	18	25	S	
$I_{C(ON)}$	$V_{GE} = 10\text{ V}, V_{CE} = 10\text{ V}$		100	A	
C_{ies}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$		2400	pF	
C_{oes}		120	pF		
C_{res}		33	pF		
Q_{ge}	$I_C = I_{C90}, V_{GE} = 15\text{ V}, V_{CE} = 0.5 V_{CES}$		106	nC	
Q_{gc}		18	nC		
Q_{gc}		32	nC		
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C25}, V_{GE} = 15\text{ V}$ $V_{CE} = 0.8 V_{CES}, R_G = R_{off} = 5\ \Omega$ Remarks: Switching times may increase for $V_{CE} \text{ (Clamp)} > 0.8 \cdot V_{CES}$, higher T_J or increased R_G		42	ns	
t_{ri}			39	ns	
$t_{d(off)}$			200	400	ns
t_{fi}			250	500	ns
E_{off}			8	12	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C25}, V_{GE} = 15\text{ V}$ $V_{CE} = 0.8 V_{CES}, R_G = R_{off} = 5\ \Omega$ Remarks: Switching times may increase for $V_{CE} \text{ (Clamp)} > 0.8 \cdot V_{CES}$, higher T_J or increased R_G		50	ns	
t_{ri}			55	ns	
E_{on}			2.0	mJ	
$t_{d(off)}$			200	ns	
t_{fi}			360	ns	
E_{off}		12	mJ		
R_{thJC}				0.5	K/W
R_{thCK}	(TO-247)		0.25		K/W

Min Recommended Footprint

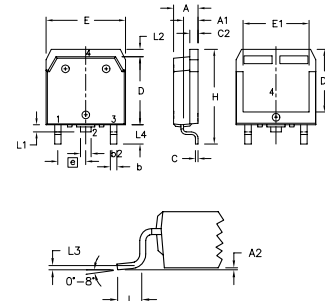


TO-247 AD Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L ₁		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

TO-268 Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.9	5.1	.193	.201
A ₁	2.7	2.9	.106	.114
A ₂	.02	.25	.001	.010
b	1.15	1.45	.045	.057
b ₂	1.9	2.1	.75	.83
C	.4	.65	.016	.026
D	13.80	14.00	.543	.551
E	15.85	16.05	.624	.632
E ₁	13.3	13.6	.524	.535
e	5.45	BSC	.215	BSC
H	18.70	19.10	.736	.752
L	2.40	2.70	.094	.106
L ₁	1.20	1.40	.047	.055
L ₂	1.00	1.15	.039	.045
L ₃		0.25		.010
L ₄	3.80	4.10	.150	.161

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592 4,881,106 5,017,508
4,850,072 4,931,844 5,034,796

5,049,961 5,187,117
5,063,307 5,237,481

5,486,275 5,306,283
5,391,023